

IN THE SPECIFICATION

Please amend the paragraph beginning on page 4, line 13, as follows:

Referring to Figure 1, a memory array 106 may be made up of rows 12 and columns 34 of memory cells 100. Each memory cell 100 may include a phase change material threshold switch 102 and a phase change memory element 104. The switch 102 controls the connection of the memory element 104 to the column or bitline 34. Thus, the switch 102 ~~12~~ operates as a selection device for the element 104 and the element 104 acts as a storage element, in accordance with one embodiment of the present invention.